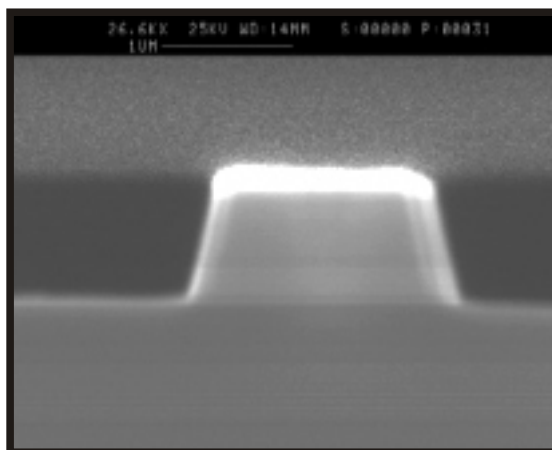


Plasmalab Data

ZnO ICP Etching



1 µm deep ZnO etch at 83° wall angle

Technology:

Inductive Coupled Plasma ICP - RIE
F based process

Results:

rate > 100 nm/ min
uniformity +/- 4 %
The mask can be SiO₂, SiN, Ni or photoresist.

Plasmalab 80 Plus

Plasmalab System 100

Plasmalab System 133

